KINETIC MODEL OF THE OXIDATION OF ZrSi₂ POWDERS

H. Geßwein^{1,2*}, A. Pfrengle^{1,2}, J. R. Binder¹ and J. Haußelt^{1,2}

¹Institute for Materials Research III, Forschungszentrum Karlsruhe GmbH, P.O. 3640, 76021 Karlsruhe, Germany ²Institute of Microsystems Engineering, University of Freiburg, Germany

The oxidation kinetics of Zr-disilicide (ZrSi₂) powders up to temperatures of 1550° C were studied in flowing air using non-isothermal and isothermal thermogravimetric (TG) analysis. During the oxidation process two main thermal events were detected. The first stage of the oxidation reaction leads to the formation of elemental silicon as an intermediate reaction product. Upon further temperature increase the newly formed silicon is oxidized. Completely oxidized ZrSi₂ samples consist of ZrSiO₄, amorphous and crystalline SiO₂ as well as some residual ZrO₂. The experimental TG data were analysed with a model-fitting kinetic method. The gas-solid reaction is complex and can best be fitted with a multi-step reaction scheme consisting of branching reactions based on 3D diffusion mechanisms and a fractal order reaction.

Keywords: kinetics, thermal oxidation, thermogravimetry, zirconium disilicide

Introduction

Several zirconium silicides with different silicon contents exist in the binary phase diagram Si-Zr [1]. These intermetallic compounds are being investigated for various high temperature applications because of their relatively low densities, high melting temperatures and good oxidation resistances at elevated temperatures. The corrosion resistance is due to the formation of a passive surface layer of SiO₂ during oxidation. According to the phase diagram, the disilicide ZrSi₂ is the compound with the highest silicon content among the phases in the Si-Zr system. ZrSi₂ crystallizes in the orthorhombic space group Cmcm and decomposes peritectically at a temperature of 1584±5°C [2]. Beside its application as a refractory compound, ZrSi₂ is an excellent choice as a reactive starting material for reaction bonding processes [3]. Reaction bonding techniques, such as the well known reaction bonding process of aluminium oxide (RBAO) [4], are based on the heterogeneous gas-solid reaction of a metal and a gaseous oxidant. Compared to conventional ceramic processing methods, reaction bonding offers the advantage of near net shape manufacturing. Due to the exceptionally high volume expansion during the gas-solid reaction of ZrSi2 with oxygen, shrinkage-free, dense ZrSiO₄ ceramics with good mechanical properties can be produced [3]. However, because of the strong exothermic oxidation reaction and the associated high volume expansion, typical process problems such as sample cracking and bloating may

occur. Knowledge of the intrinsic oxidation kinetics can be helpful to avoid these problems.

There are not many published reports on the oxidation behaviour of ZrSi2 in powder form [5, 6] and kinetic parameters for the complex oxidation process are unavailable to the best of the authors' knowledge. In the present paper, we report of the oxidation behaviour of ZrSi₂ powders in flowing air at temperatures up to 1550°C. A model-fitting kinetic analysis of the non-isothermal and isothermal oxidation of ZrSi₂ powders is presented employing thermogravimetry. The Netzsch Thermokinetics software package is used for the non-linear regression model-fitting analysis [7]. The aim of this model-fitting kinetic approach is to find a kinetic model with minimal adjustable parameters which quantitatively describes the kinetics of the complete oxidation reaction of the disilicide particles. This formal kinetic model can then be used to predict the progress of reaction under any heating profiles. From the technical aspect this data reduction is very valuable for process control and optimization, which is an important issue regarding the fabrication of defect-free reaction bonded oxide ceramics using this intermetallic compound [3, 8].

Experimental

The investigated material is zirconium disilicide $ZrSi_2$ (H.C. Starck) in powder form. To reduce the particle size, the as-received powder was milled in a Netzsch agitator mill (LMK 4, ZrO_2 milling balls and 2-propanol

* Author for correspondence: holger.gesswein@imf.fzk.de

as milling media). The milled material has a specific surface area of 5.4 m² g⁻¹. An average particle size of $d_{50}=0.9 \ \mu\text{m}$ and $d_{90}=2.1 \ \mu\text{m}$ was determined using a laser-scattering particle-size-distribution analyser (Microtrac X 100).

Simultaneous TG/DTA experiments with a heating rate of 10°C min⁻¹ up to temperatures of 1450°C were conducted using a Netzsch STA 449C instrument. The atmosphere was flowing artificial air $(20.5\% O_2 \text{ in } N_2)$ at a rate of 50 mL min⁻¹. Sample sizes of approximately 20 mg were contained in the manufacturer's alumina crucibles (volume: 85 µL). For phase analysis and determination of the maximum mass change after complete ZrSi2 oxidation, samples were oxidized at temperatures of 600, 700, 800, 900, 1000 and 1600°C for 4 h in a box furnace (Carbolite RHF 1700). Oxidized ZrSi₂ samples were then characterised by means of X-ray powder diffraction using a Siemens diffractometer (Model D5005) with CuK_{α} radiation and a solid state detector (Bruker Sol-X). The operating conditions were 40 kV and 40 mA in the angular range $15-70^{\circ}$ in 20. Crystalline phase identification based on the XRD patterns was aided by the ICDD-PDF-2 database.

For kinetic analysis, a series of experiments was conducted in a Netzsch TG/DTA thermal analyser (STA 409, flowing artificial air $(20.5\% O_2 \text{ in } N_2)$ at a rate of 100 mL min⁻¹). To obtain a better weighing accuracy, larger sample masses of approximately 50 mg were filled into the manufacturer's TG/DTA alumina crucibles (volume: ~350 µL). The TG baselines were corrected by subtraction of predetermined baselines run under identical conditions except for the absence of sample. The samples were heated up to 1550°C with programmed heating rates of 1, 2.5, 5 and 10°C min⁻¹ followed by an isothermal hold of 4 h to ensure almost complete oxidation. Additionally isothermal runs were performed at temperatures of 500, 600, 700 and 800°C for several hours. A constant heating rate of 20°C min⁻¹ to the desired oxidation temperature was used in the isothermal runs. The experimental mass change data were transformed to conversion data by using Eq. (1):

$$\alpha(t) = \frac{m_0 - m_t}{m_0 - m_{end}} \tag{1}$$

where α is the general variable reaction degree, m_0 is the starting sample mass, m_t the sample mass at time *t* and m_{end} is the sample mass after complete oxidation. Then different kinetic models were fitted to these conversion data to extract the kinetic parameters.

Results and discussion

ZrSi₂ powder characterisation

Figure 1 shows a SEM micrograph of the investigated milled ZrSi₂ powders. The particles have an irregular morphology with sizes ranging between 1 and 3 µm, which is in reasonable agreement with the laser diffractometry measurements. Assuming spherical particles, the relation d_{BET} =6/ ρS_{BET} , where ρ is the theoretical density of ZrSi₂ (ρ =4.88 g cm⁻³) and S_{BET} is the BET surface area, holds. From the BET surface area an average grain diameter d_{BET} of 0.2 µm can be calculated. This is an effective particle size, describing the reactivity of the powder. The small value results from the fractured surfaces of the brittle intermetallic particles. The theoretical mass gain during complete ZrSi₂ oxidation assuming following equation:

$$ZrSi_2+3O_2 \rightarrow ZrO_2+2SiO_2$$
 (2)

is 65.1 mass%. The experimentally determined maximum mass gain after complete oxidation of the milled powder in a box furnace at 1600°C for 4 h is approximately 60.9 mass%, indicating a pre-oxidation of the disilicide during powder synthesis and milling. The XRD pattern of the milled powder in Fig. 2 shows reflections of ZrSi₂ only and some very weak reflections of ZrSi and Si as impurities. From



Fig. 1 SEM micrograph of agitator milled ZrSi₂ powder



Fig. 2 XRD pattern of milled ZrSi₂ powder. All peaks correspond to the orthorhombic ZrSi₂ phase. The inset shows additional very weak reflexes of impurities of ZrSi and Si

Rietveld refinement of the diffraction pattern the mass fractions of ZrSi and Si are estimated to be 3 and 2 mass%, respectively. Other impurity phases as well as the presence of oxidized surface layers of the powder particles, which may have been formed during milling, were not detected by XRD.

Oxidation products

Oxidation products were determined from powder X-ray diffraction profiles. Figure 3 displays X-ray diffraction patterns of ZrSi₂ powders oxidized at 600, 700, 800, 900 and 1000°C for 4 h in a box furnace. To emphasize the low intensity diffraction peaks and the high background, a logarithmic scale for the intensity



Fig. 3 XRD patterns of ZrSi₂ powder oxidized at a – 600°C, b – 700°C, c – 800°C, d – 900°C and e – 1000°C for 4 h under flowing air in a box furnace (ZS: ZrSi₂, S: Si, t: t-ZrO₂, m: m-ZrO₂)



Fig. 4 Progress of the intensity of the (220) peak of Si for samples oxidized at different temperatures

is used. The X-ray patterns of samples exposed at temperatures of 600 and 700°C show intense diffraction peaks of unreacted ZrSi₂, as well as the presence of monoclinic and tetragonal ZrO₂. The intensity of the strongest (131) reflex of ZrSi2 at 39.1° 20 decreases continuously with increasing oxidation temperature. At a temperature of 1000°C almost all $ZrSi_2$ is oxidized. This diffraction pattern mainly consists of broad peaks of monoclinic and tetragonal ZrO₂. The high background in the XRD patterns suggests the presence of amorphous oxidation products. The broad 'halo' in the different patterns located between 15 and $30^{\circ} 2\theta$ is shifted to smaller scattering angles with increasing oxidation temperatures indicating a change in the composition and stoichiometry of the amorphous phase. At lower oxidation temperatures the 'halo' is located at about 30° 20, indicating an amorphous ZrO₂ phase, whereas at higher temperatures more amorphous SiO₂ is formed and the 'halo' is located at approximately 20° 20. During the oxidation process elemental Si is formed as an intermediate product. The progress of the intensity of the (220) peak of Si at different oxidation temperatures is shown in Fig. 4. As can be seen, the amount of Si increases up to a temperature of 800°C, whereas at higher oxidation temperatures the intensity of the (220) peak decreases continuously due to the oxidation of the newly formed Si to amorphous SiO_x. ZrSi₂ samples completely oxidized at 1600°C for 4 h consist of ZrSiO₄, amorphous and crystalline SiO_2 as well as some residual ZrO_2 .

The XRD results demonstrate that $ZrSi_2$ is oxidized according to the Wagner theory of selective oxidation [10–12] in which the less noble constituent of an alloy is selectively or preferentially oxidized. In the Si–Zr system silicon is more noble than zirconium and therefore silicon escapes oxidation by diffusing from the oxide layer into the bulk of the compound. Zirconium, as the less noble metal, is selectively oxidized forming an outer oxide layer. $ZrSi_2$ is the compound with the highest silicon content in the Sr–Zr system and therefore the selective oxidation results in the formation of elemental Si.

Simultaneous TG/DTA

The typical thermal profile of the oxidation of $ZrSi_2$ powder, obtained by simultaneous TG/DTA in flowing air, is presented in Fig. 5. The shape of the DTG curve corresponds to the DTA curve, which shows that the mass gain rate can be attributed to the observed exothermic effects. In general, two main thermal events can be clearly distinguished. Oxidation starts at a temperature of approximately 500°C and the sample mass increases continuously up to 900°C. The associated DTA and DTG peak maxima are located at approxi-

Table 1	$f(\alpha)$	functions	for	the n	nost	common	mechanisms	in	heterogeneous	kinet	ics
	~ ~ /								0		

Model	Symbol	$f(\alpha)$
One-dimensional diffusion	D1	1/2α
Two-dimensional diffusion	D2	$-(1/\ln(1-\alpha))$
Three-dimensional diffusion (Jander)	D3	$3(1-\alpha)^{2/3}/2[1-(1-\alpha)^{1/3}]$
Three-dimensional diffusion (Ginstling-Brounshtein)	D4	$3/2[(1-\alpha)^{-1/3}-1]$
Three-dimensional diffusion (exact solution of Fick's law)	D3F	see appendix
<i>n</i> th order	Fn	$(1-\alpha)^n$
Phase boundary controlled	$\operatorname{Rn}(1 \le n \le 3)$	$n(1-\alpha)^{1-1/n}$
Nucleation and growth (Avrami-Erofeev)	An(0.5 ≤ <i>n</i> ≤4)	$n(1-\alpha)[-\ln(1-\alpha)]^{1-1/n}$

Table 2 Kinetic results derived from non-linear regression for the best fitting two-step model based on two consecutive reactions ($A \rightarrow B \rightarrow C$). For the definition of the kinetic parameters see [9]

	Reaction type	Parameter	Value	Correlation- coefficient
d:f	D3F	$\log(A_1/\mathrm{s}^{-1})$	4.437±0.152	0.99812
		$E_{\rm a1}$ / kJ mol ⁻¹	179±3	
	D3F	$\log(A_2/\mathrm{s}^{-1})$	1.087±0.289	
		$E_{\rm a2}$ /kJ mol ⁻¹	168±8	
		FollReact1	0.76±0.01	

d:f: two consecutive steps, FollReact1: share of step 1 in the total mass increase





mately 840°C. This first part of the oxidation process has a mass gain of approximately 45%. With increasing temperature a second oxidation process with a mass change of approximately 14% and a much lower mass gain rate compared to the first step can be observed. According to the XRD results the first oxidation step can be associated with the selective oxidation of $ZrSi_2$ to ZrO_2 , SiO_x and elemental Si. The observed mass change of approximately 45% is slightly higher than the theoretical value of 43.3% for the oxidation reaction represented by Eq. (3a):

$$ZrSi_2 \rightarrow ZrO_2 + SiO_2 + Si$$
 (3a)

The second oxidation step which is observed at higher temperatures can be attributed to the oxidation of elemental Si, which has been formed during the selective oxidation reaction. This oxidation step can be represented by Eq. (3b):

$$ZrO_2 + SiO_2 + Si \rightarrow ZrO_2 + 2SiO_2$$
 (3b)

and is associated with a theoretical mass change of 15.2%. The sharp DTA/DTG peak at 1420°C and the corresponding small mass increase indicate an increased reactivity of the almost completely oxidized disilicide particles. This is most likely due to the cracking of the protective oxide layer, resulting from the formation of $ZrSiO_4$ from the newly formed SiO₂ and ZrO₂.

From the XRD and TG/DTA results it is evident that the reaction mechanism of the gas-solid oxidation of the $ZrSi_2$ particles is complex and changes during the course of reaction. Thus, it seems unlikely that this complex overall reaction can be described with a simple single-step reactin. Therefore, a multi-step

 Table 3 Kinetic results derived from non-linear regression for the best fitting three-step model. For the definition of the kinetic parameters see [9]

	Reaction type	Parameter	Value	Correlation- coefficient
t:c,p	D3F	$\log(A_1/\mathrm{s}^{-1})$	0.768±0.515	0.99948
		$E_{\rm al}/{\rm kJ}~{\rm mol}^{-1}$	125±9	
	D3F	$\log(A_2/\mathrm{s}^{-1})$	8.363±0.240	
		$E_{\rm a2}/{\rm kJ}~{\rm mol}^{-1}$	257±5	
	Fn	$\log(A_3/\mathrm{s}^{-1})$	2.928±0.207	
		$E_{\rm a3}/{\rm kJ}~{\rm mol}^{-1}$	170±5	
		п	2.3±0.1	
		FollReact2	$0.733 {\pm} 0.007$	

t:c,p: three-step model, consisting of concurrent and parallel reactions

FollReact2: share of reaction pathway 2 in the total mass increase

model-fitting approach is used to describe the reaction kinetics. This is discussed in the next paragraph. Such a model-fitting approach was also successfully applied to describe the oxidation kinetics of the intermetallic compound ZrAl₃ [13] as well as the oxidation kinetics of magnetite using simultaneous TG/DSC data [14].

Oxidation kinetics

In thermal analysis the kinetics of solid-state reactions are generally described in terms of a 'kinetic triplet' E, A and $f(\alpha)$ according to the following equation:

$$\frac{\mathrm{d}\alpha}{\mathrm{d}t} = k(T)f(\alpha) = A\exp\left(-\frac{E_{\mathrm{a}}}{RT}\right)f(\alpha) \qquad (4)$$

where α is the conversion degree, in thermogravimetric studies defined as in Eq. (1), t the time, T the temperature, k(T) the rate constant, A the pre-exponential factor, E_a the apparent activation energy and R is the gas constant. For non-isothermal data obtained at a constant heating rate $\beta = dT/dt$, $d\alpha/dt$ in Eq. 4 is replaced with $\beta d\alpha/dT$. The above equation may be extended to describe complex processes such as concurrent or consecutive reactions, each with its own kinetic triplet. The reaction models $f(\alpha)$, most commonly used in heterogeneous kinetics, are listed in Table 1. The full data sets which serve as input to the kinetics software are presented in Fig. 6.

Because it has been established in the previous sections, that elemental Si is formed as an intermediate phase in the oxidation $ZrSi_2$ and because of the complex multistage process, visible in the TG curves, attempts were made to fit a range of multi-step processes to the thermogravimetric data. A model-free isoconversion method (the results from this analysis are not included in this paper) was used for an initial estimate of the kinetic parameters. These values were then used as



Fig. 6 Non-isothermal TG curves with holding time of 4 h at 1550°C and isothermal TG curves for the oxidation of ZrSi₂ powder

starting parameters for the non-linear regression model-fitting procedure.

Fitting a variety of different consecutive and branching two-step processes, based on either diffusion (D3F, D4, D3), phase boundary (R3, R2) or *n*-th order reactions (Fn), yielded only a poor description of the experimental TG data. This is demonstrated in Fig. 7, where the best fitting results for a two-step oxidation model according to Eqs (3a) and (3b), based on diffusion reactions of the type D3F are shown. As can be seen from Fig. 7a, the influence of the heating rateon the mass change of the first oxidation step cannot reproduced correctly. The corresponding kinetic parameters are summarised in Table 2.

Therefore, a third step was allowed in the modelling, which introduces an additional degree of freedom. With three-step processes the quality of the fit improved significantly and the complex features of the TG data, in particular the influence of the heating rate on the mass gain of the first oxidation step (Fig. 8a), which is an indication of a branched reaction pathway [7], can be satisfactorily reproduced. The best fitting three-step model consists of two concurrent and one parallel reaction step based on 3D diffusion mechanisms (D3F) and a fractal reaction order (Fn). The underlying differential equations for this model are:

- \

$$\frac{\mathrm{d}a}{\mathrm{d}t} = -A_1 \exp\left(-\frac{E_1}{RT}\right) f(a) - A_2 \exp\left(-\frac{E_2}{RT}\right) f(a)$$

$$\frac{\mathrm{d}b}{\mathrm{d}t} = A_1 \exp\left(-\frac{E_1}{RT}\right) f(a) + A_3 \exp\left(-\frac{E_3}{RT}\right) f(c) \qquad (5)$$

$$\frac{\mathrm{d}c}{\mathrm{d}t} = A_2 \exp\left(-\frac{E_2}{RT}\right) f(a) - A_3 \exp\left(-\frac{E_3}{RT}\right) f(c)$$

where a, b, c are the relative concentrations of the educt, final product and intermediate reaction product, respectively. The D3F diffusion model implemented in the Thermokinetics software is an approximation for the exact solution of Fick's law [15]. The appropriate equations for this reaction type are given in the appendix. The intermediate and final products of this formal multi-step kinetic model are to be viewed as pseudocomponents and may comprise different chemical species, but these pseudo-components can be linked with the actually occurring intermediate phases and products formed during the oxidation of ZrSi₂. The results from the non-linear regression analysis are summarised in Table 3 and a comparison of measured and calculated degree of reaction is given in Fig. 8. The overall agreement is very good over the entire reaction extent and simultaneously matches the shift in profile location with heating rate as well as the isothermal profiles.

The branching reaction pathway may be explained by the simultaneous occurrence of two oxidation



Fig. 7 Comparison of measured and calculated reaction extent for a two-step oxidation model ($A \rightarrow B \rightarrow C$) according to Eqs (3a) and (3b), based on diffusion reactions of the type D3F. (a – constant heating rate data with holding time and b – isothermal data; symbols: measured, lines: calculated)

mechanisms during the first stage of $ZrSi_2$ oxidation, as represented schematically by Eq. (6a) and (6b):

$$ZrSi_2 \xrightarrow{O_2} ZrO_2 + 2Si$$
 (6a)

$$ZrSi_2 \xrightarrow{O_2} ZrO_2 + 2SiO_2$$
 (6b)

Equation (6a) corresponds to the selective oxidation of zirconium in the intermetallic compound. Concurrently to this selective oxidation reaction of zirconium, the more noble constituent, silicon, of the intermetallic compound is already oxidized (Eq. (6b)). Consequently ZrSi₂ oxidation proceeds in a not purely selective manner, but as concurring selective and nonselective oxidation mechanisms. The agreement of the results with the branched reaction mechanism consisting of two D3F equations is an indication that the rate controlling step is the diffusion of different chemical species through the growing multiphase oxide layer. In a third step the newly formed Si is oxidized to SiO₂. This third oxidation step occurs at higher temperatures and for complete-oxidation of the ZrSi₂ powder particles temperatures up to 1550°C are necessary. An explanation for the observed consistency with a fractal order reaction for the third step cannot be given unambiguously because the physical properties of the multi oxide film change during the last stage of the oxidation reaction. At this stage the phase formation of zircon (ZrSiO₄) takes place, which is associated with a change of the diffusion coefficients in the oxide film and it is likely that the oxide film cracks due to mechanical stresses developed during the oxidation reactions, in particular at the higher heating rates.

According to the Xray, TG/DTA and kinetic results, following reaction scheme for the complete oxidation of ZrSi₂ particles in flowing air is proposed:

$$ZrSi_{2} \xrightarrow[T>500^{\circ}]{O_{2}} ZrO_{2} + (2-y)SiO_{x} + ySi_{\overline{T>800^{\circ}}} O_{2}$$
(7)
$$ZrO_{2} + 2SiO_{2}$$

whereas the first oxidation step of Eq. (7) is a combination of the two concurrent reactions (6a)



Fig. 8 Comparison of measured and calculated reaction extent for the best fit branching three-step oxidation of $ZrSi_2$ using the parameters in Table 3. Steps 1 and 2 invoke the D3F diffusion equation and step 3 the n^{th} order equation. (a – constant heating rate data with holding time and b – isothermal data; symbols: measured, lines: calculated)

and (6b). Finally, at temperatures of about 1300°C the formation of $ZrSiO_4$ begins to take place and after complete oxidation, the $ZrSi_2$ samples consist of $ZrSiO_4$, amorphous and crystalline SiO₂, as well as some residual ZrO_2 . It should be stressed, however, that the determined kinetic parameters, in particular the pre-exponential Arrhenius factor, which is highly dependent on the particle size, are only valid for the investigated experimental conditions such as gas atmosphere, temperature range and powder particle size.

Conclusions

Non-isothermal and isothermal thermogravimetry was used to investigate the heterogeneous gas-solid oxidation of ZrSi₂ powder under flowing air up to temperatures of 1550°C. The experimental TG curves clearly suggest a well resolved, multi-step process for the oxidation and therefore a model-fitting kinetic analysis based on multivariate non-linear regression was conducted. The selective oxidation of ZrSi₂ results in the formation of elemental Si, ZrO2 and SiOx as intermediate oxidation products which are further oxidized with increasing temperature. The complex overall reaction can be best described with a three-step reaction scheme consisting of two branching reactions of the type D3F followed by a fractal order reaction Fn. The two branching reactions can be associated with the simultaneous occurrence of two concurrent oxidation mechanisms. In one reaction pathway ZrSi2 is selectively oxidized to ZrO₂ and Si. The other pathway is described by the non-selective oxidation of ZrSi₂ to ZrO₂ and SiO_x. At higher temperatures the selectively formed Si is further oxidized in a third step. The determined kinetic model can be used for process control and optimisation and can be readily incorporated into more complicated source and sink models for real applications like the reaction bonding of zircon-based ceramics or zirconia-alumina-mullite ceramics by the direct oxidation of ZrAl₃/ZrSi₂ powder compacts.

Appendix

The approximation formula used in the Thermokinetics software for the exact solution of Fick's law for the three dimensional case (D3F) is:

$$f(\alpha) = 4.62755136 \begin{cases} \exp(-1.05640725\ln(0.1)) \\ \text{for } \alpha \ge 0.1 \\ \exp(-1.05640725\ln(0.1)) \\ (1-\alpha)/0.9/ \\ [1.0+9.608828(\alpha-0.1)^2 - \\ -3.5600323(\alpha-1)^3] \text{ for } \alpha \ge 0.1 \end{cases}$$

References

- H. M. Ondik and H. F. McMurdie, Phase Diagrams for Zirconium + Zirconia Systems, The American Ceramic Society 1998, p. 423.
- 2 H. Okamato, Bull. Alloy Phase Diagrams, 11 (1990) 513.
- 3 V. D. Hennige, J. Haußelt, H.-J. Ritzhaupt-Kleissl and T. Windmann, J. Eur. Ceram. Soc., 19 (1999) 2901.
- 4 N. Claussen, T. Le and S. Wu, J. Eur. Ceram. Soc., 5 (1989) 29.
- 5 O. Hönigschmid, Monatsh. Chem., 27 (1906) 1069.
- 6 V. A. Lavrenko, V. Zh. Shemet and A. V. Goncharuk, Thermochim. Acta, 93 (1985) 501.
- 7 J. Opfermann, Netzsch Thermokinetics 2, Version 2004.05, Netzsch Gerätebau GmbH.
- 8 H. Geßwein, J. R. Binder, H.-J. Ritzhaupt-Kleissl and J. Haußelt, J. Eur. Ceram. Soc., 26 (2006) 697.
- 9 J. Opfermann, J. Therm. Anal. Cal., 60 (2000) 641.
- 10 C. Wagner, J. Electrochem. Soc., 99 (1952) 368.
- 11 C. Wagner, J. Electrochem. Soc., 103 (1956) 627.
- 12 C. Wagner, Z. Electrochemie, 63 (1959) 773.
- H. Geßwein and J. R. Binder, Thermochim. Acta, 444 (2006) 6.
- [14] J. P. Sanders and P. K. Gallagher, J. Therm. Anal. Cal., 72 (2003) 777.
- 15 B. Serin and T. Ellickson, J. Chem. Phys., 9 (1941) 742.

Received: March 21, 2007 Accepted: June 12, 2007 OnlineFirst: October 13, 2007

DOI: 10.1007/s10973-007-8461-5